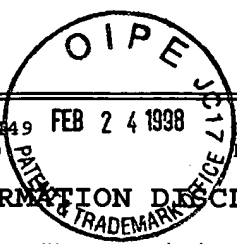


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Form PTO-1449 FEB 24 1998 U.S. Department of Commerce
(Rev. 8-83) Patent and Trademark Office

Attorney Docket N. 0756-1614	Serial N. 08/781,920
Applicant: Takashi FUKUNAGA et al	
Filing Date: Dec 30, 1996	Group: 1442-1762

INFORMATION DISCLOSURE STATEMENT

(Use several sheets if necessary)

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Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date (if appropriate)
	5,426,064	06/20/95	Zhang et al			
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						Yes	No

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

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Attorney Docket N. 0756-1614

Serial No. 08/781,920

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Applicant: Takeshi FUKUNAGA et al

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Group: 1112

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Attorney Docket N . 0756-1614

Serial N . 08/781,920

INFORMATION DISCLOSURE STATEMENT

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Applicant: Takeshi FUKUNAGA et al.

Filing Date: Dec. 30, 1996

Group: 4442- 1762

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[Signature]	5,597,741	01/28/97	Sakamoto et al.	438	486	
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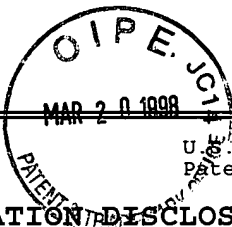
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						Yes	No

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